

July 2000

FDP6030BL/FDB6030BL

N-Channel Logic Level PowerTrench® MOSFET

General Description

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

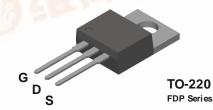
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\text{DS(on)}}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

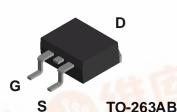
Features

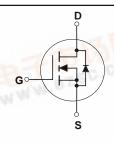
- 40 A, 30 V. $R_{DS(ON)}=0.018~\Omega~@~V_{GS}=10~V$ $R_{DS(ON)}=0.024~\Omega~@~V_{GS}=4.5~V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low R_{DS(ON)}.

FDB Series

• 175°C maximum junction temperature rating.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FDP6030BL	FDB6030BL	Units				
V _{DSS}	Drain-Source Voltage	3	30	V				
V _{GSS}	Gate-Source Voltage	±	±20					
I _D	Maximum Drain Current - Continuous (Note 1)	4	40					
	- Pulsed	1	20	20.00				
P _D	Total Power Dissipation @ T _C = 25°C		W					
	Derate above 25°C	0.	W/°C					
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-65 to	°C					
Thermal Characteristics								
$R_{\theta_{JC}}$	Thermal Resistance, Junction-to-Case	2	5	°C/W				
RθJA	Thermal Resistance, Junction-to-Ambient	62	2.5	°C/W				

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB6030BL	FDB6030BL	13"	24mm	800
FDP6030BL	FDP6030BL	Tube	N/A	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RAT	INGS (Note 1)				
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15 \text{ V}, I_D = 40 \text{ A}$			150	mJ
I _{AR}	Maximum Drain-Source Avalnche	Current			40	Α
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
ΔBVnss ΔT	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μд
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 1)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.6	3	V
$\Delta V_{GS(th)}$ ΔT_1	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		-4.5		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$		0.015 0.021 0.019	0.018 0.030 0.024	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 10 V	40			Α
g FS	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		30		S
Dvnamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		1160		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		250		pF
C_{rss}	Reverse Transfer Capacitance			100		pF
Switchin	g Characteristics (Note 1)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 1 \text{ A},$		9	17	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_{GEN} = 6 Ω		11	20	ns
t _{d(off)}	Turn-Off Delay Time			23	37	ns
t _f	Turn-Off Fall Time			8	16	ns
Qg	Total Gate Charge	V _{DS} = 15 V,		12	17	nC
Q _{gs}	Gate-Source Charge	$I_D = 20 \text{ A}, V_{GS} = 5 \text{ V}$		3.2		nC
Q_{gd}	Gate-Drain Charge			3.7		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
l _s	Maximum Continuous Drain-Source				40	А
V _{SD}	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V}, I_S = 20 \text{ A}$ (Note 1)		0.95	1.2	V

Note: 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics

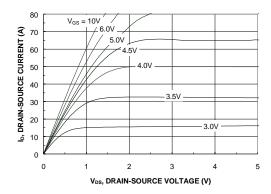


Figure 1. On-Region Characteristics.

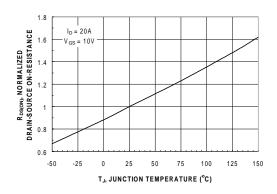


Figure 3. On-Resistance Variation with Temperature.

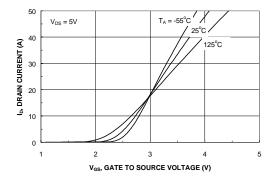


Figure 5. Transfer Characteristics.

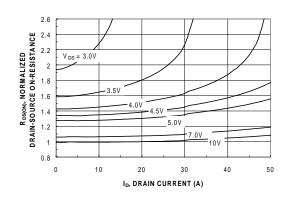


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

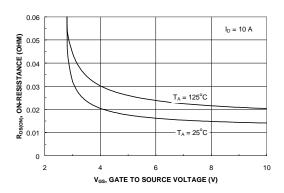


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

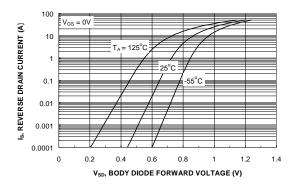
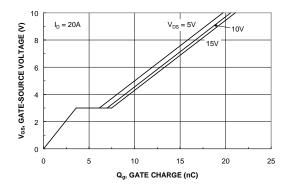


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



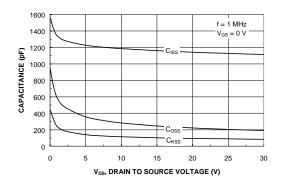
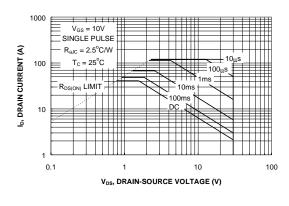


Figure 7. Gate-Charge Characteristics.





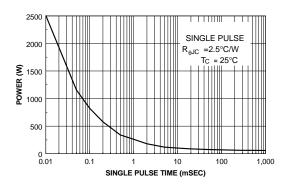


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

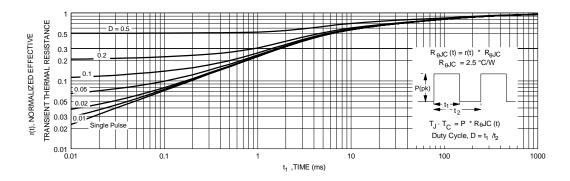
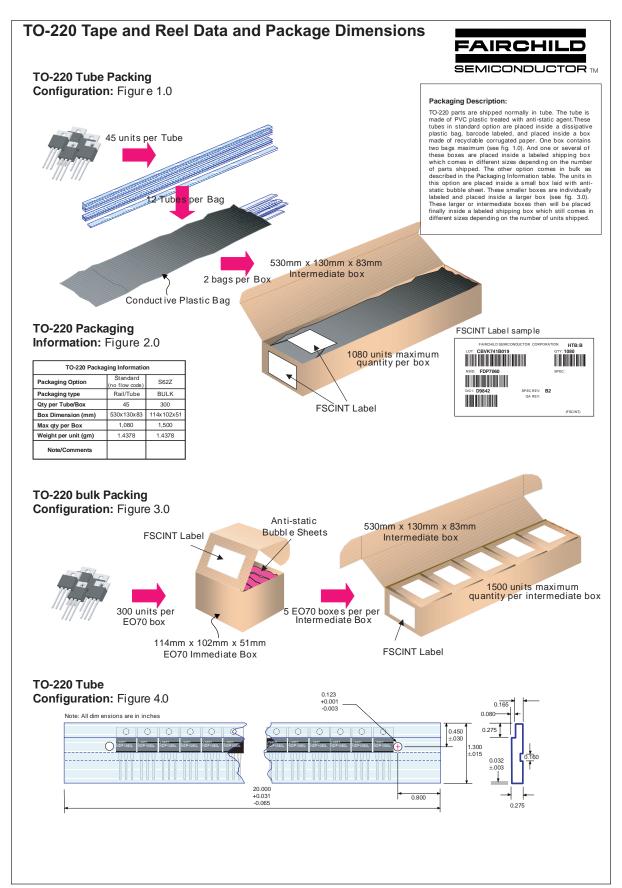
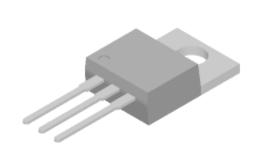


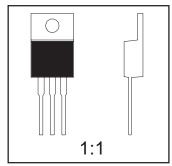
Figure 11. Transient Thermal Response Curve.



TO-220 Tape and Reel Data and Package Dimensions, continued

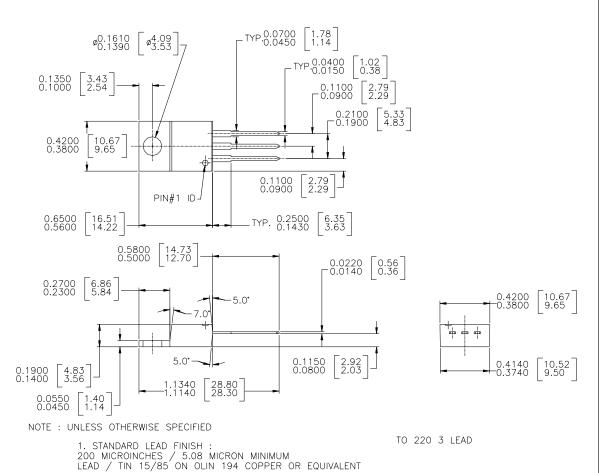
TO-220 (FS PKG Code 37)



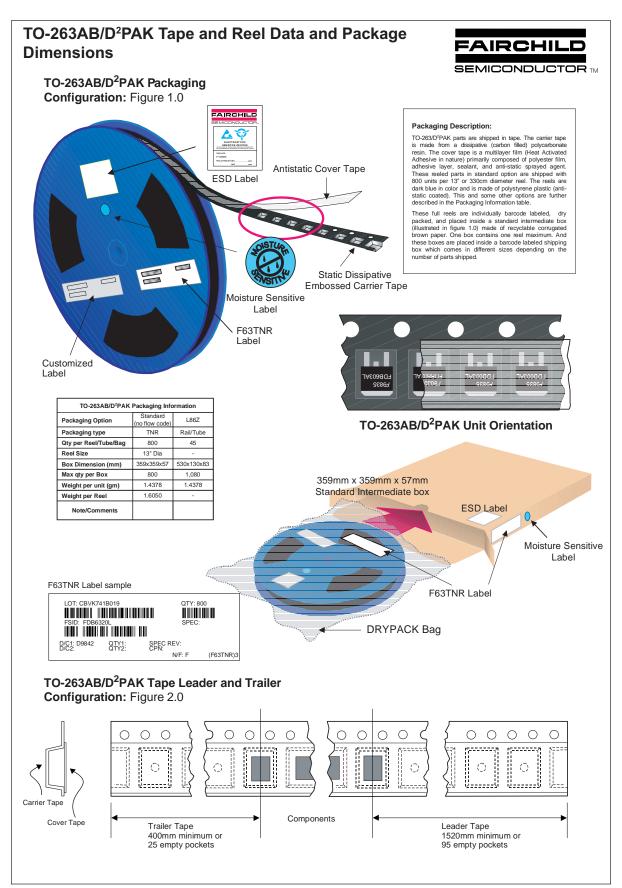


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 1.4378

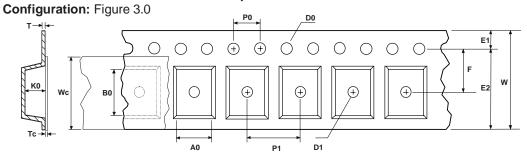


2. DIMENSION BASED ON JEDEC STANDARD TO-220 VARIATION AB, ISSUE J, DATED 3/24/87



TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape



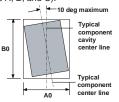
User Direction of Feed

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D²PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

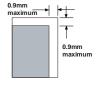
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

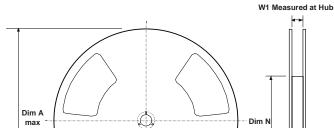


Sketch B (Top View)
Component Rotation

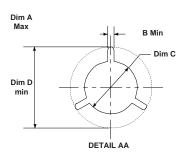


Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0







W2 max Measured at Hub

⊷ W3

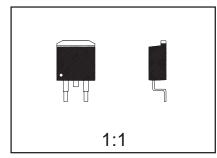
See detail AA

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

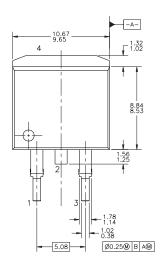
TO-263AB/D²PAK (FS PKG Code 45)

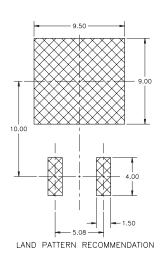


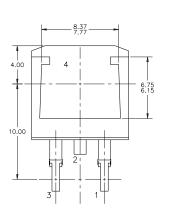


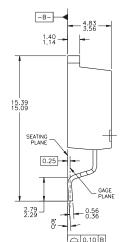
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









- NOTES: UNLESS OTHERWISE SPECIFIED

 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) STANDARD LEAD FINISH:
 200 MICROINCHES / 5.08 MICROMETERS MIN.
 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
 D) NO PACKAGE CHIPS, CRACKS OR SURFACE
 IDENTIFICATION ALLOWED AFTER FORMING.
 E) REFERENCE JEDEC, TO—263, ISSUE C,
 VARIATION AB, DATED 2/92.

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 $\begin{array}{lll} \mathsf{FACT} \ \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} & \mathsf{QS^{\mathsf{TM}}} \\ \mathsf{FAST}^{\texttt{\$}} & \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} \\ \mathsf{FASTr^{\mathsf{TM}}} & \mathsf{Super} \mathsf{SOT^{\mathsf{TM}}}\text{-3} \\ \end{array}$

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

SuperSOT™-8

SyncFET™

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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